Key l 2

Symbol	Parameter	Values	Unit
CES	Collector-emitter voltage	650	V
GES	Gate-emitter voltage	±20	V
C	Continuous collector current (C=25)	12	A
	Continuous collector current (C=100)	6	A!
CM	Pulsed collector current, p limited by vjmax	24	A
F	Diode continuous forward current (C=100)	6	A
FM	Diode maximum current, p limited by vjmax	24	A
sc	Short circuit withstand time	10	µs
tot	Power dissipation (C=25)	136	W
	Power dissipation (C=100)	68	W
vj	Operating junction temperature range	-40 to +175	
stg	Storage temperature range	-55 to +150	

Symbol	Parameter	Values		Unit
		Typ.	Max.	
th(j-c)	Therma			

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
$_{CES}$	Collector-emitter breakdown voltage	$_{GE}$=0V, $_{C}$=250μA	650			

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
$t_{d(on)}$	Turn-on delay time		-	10	-	ns
t_r	Rise time		-	8		
		V_{CC}=400V V_{GE}=0/15V I_C=6A R_G=10 Inductive load				

Symbol	Parameter

Typical performance characteristics

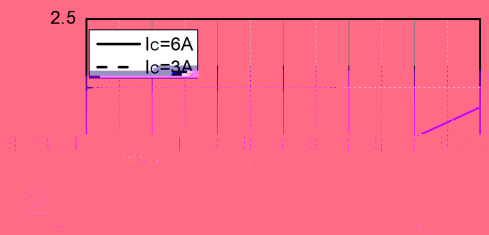

Fig 7. Typical $_{CEsat}$ as a function of $_{vj}$

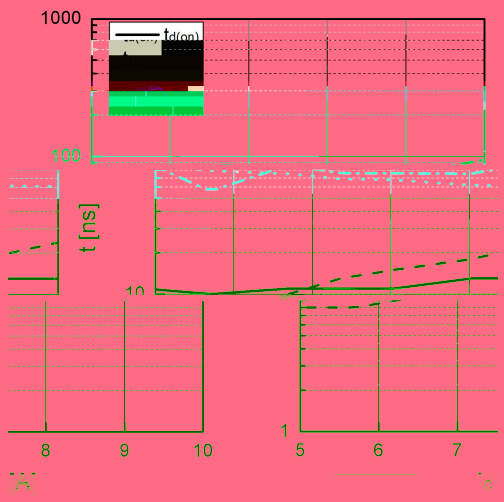

Fig 8. Typical switching time as a function of $_{C}$

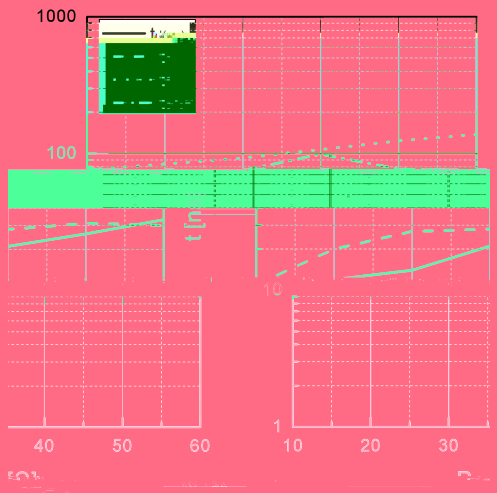

Fig 9. Typical switching times as a function of $_{G}$

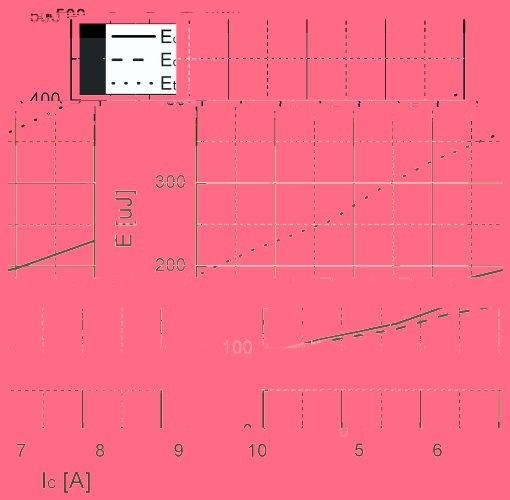

Fig 10. Typical switching energy losses as a function of $_{C}$

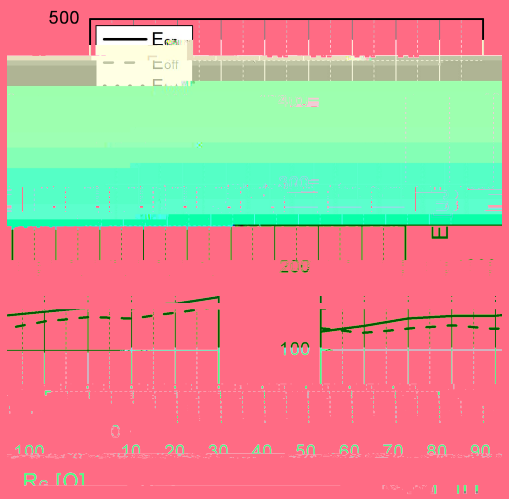

Fig 11. Typical switching energy losses as a function of $_{G}$

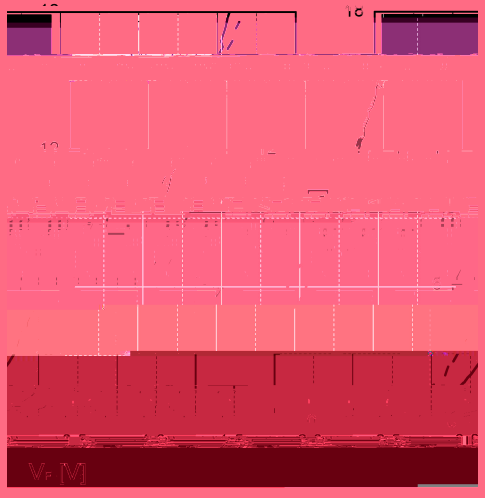

Fig 12. Typical $_{F}$ as a function of $_{F}$

Typical performance characteristics

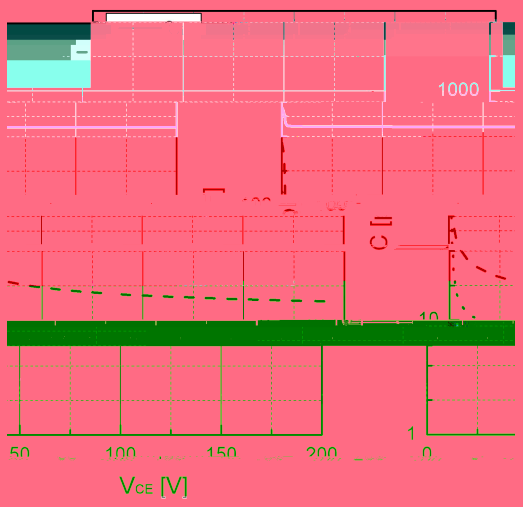

Fig 13. Typical capacitance as a function of $_{CE}$ (f=1Mhz, $_{GE}$=0V)

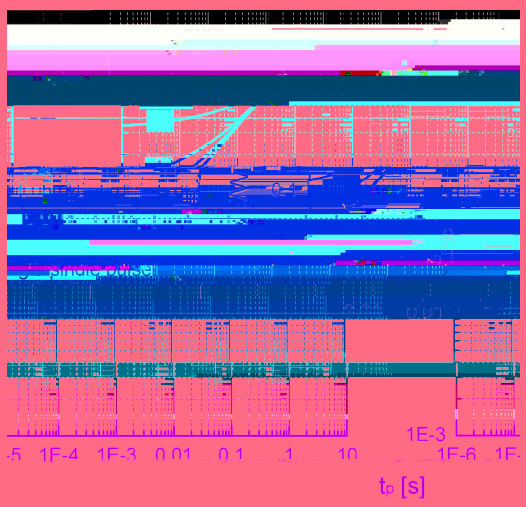

Fig 14. Transient thermal impedance of IGBT

Dimensions						
Ref.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90	-	10.20	0.390	-	0.402
B	14.70	-	15.80	0.579	-	0.622
C	9.4	-	9.6	0.37	-	0.378
D	-	2.54	-	-	0.100	-
E	1.20	-	1.40	0.047	-	0.055
F	0.75	-	0.85	0.029	-	0.033
G	-	-	1.75	-	-	0.069
H	4.40	-	4.70			

Date	Revision	Changes
2024-06-25	Rev 1.0	Release of the datasheet
2025-02-06	Rev 1.1	Update
2025-04-08	Rev 1.2	Character Update

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